Ordering number: EN 2392A

SANYO

No.2392A

2SK772

N-Channel Junction Silicon FET

AF Amp Applications

Applications

Variable resistors, analog switches, AF amp, constant-current circuit

Features

Adoption of FBET process

Absolute Maximum Ratings at Ta=25°C

			unit
Drain to Source Voltage	V_{DSX}	40	V
Gate to Source Voltage	V_{GDS}	-40	V
Gate Current	I_G	10	mA
Drain Current	I_D	20	mA
Allowable Power Dissipation	P_D	300	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

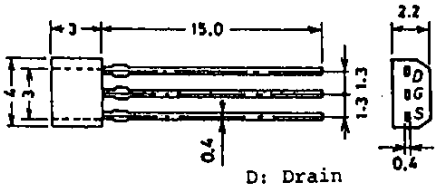
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Gate to Drain Breakdown Voltage	$V_{(BR)GDS}$	I_G=-10μA, V_{DS}=0	-40			V
Gate Cutoff Current	I_{GSS}	V_{GS}=-20V, V_{DS}=0			-1.0	nA
Cutoff Voltage	$I_{GS(off)}$	V_{DS}=10V, I_D=1μA	-0.3	-0.9	-2.5	V
Drain Current	I_{DSS}	V_{DS}=10V, V_{GS}=0	1.2*		12.0*	mA
Forward Transfer Admittance	$\|Y_{fs}\|$	V_{DS}=10V, V_{GS}=0, f=1kHz	4.5	9.0		mS
Input Capacitance	C_{iss}	V_{DS}=10V, V_{GS}=0, f=1MHz		9.0		pF
Reverse Transfer Capacitance	C_{rss}	V_{DS}=10V, V_{GS}=0, f=1MHz		2.1		pF
Noise Figure	NF	V_{DS}=10V, Rg=1kΩ, I_D=1mA, f=1kHz		1.5		dB

*: The 2SK772 is classified by I_{DSS} as follows: (unit: mA)

1.2	D	3.0	2.5	E	6.0	5.0	F	12.0

Package Dimensions 2034
(unit: mm)



D: Drain
G: Gate
S: Source

SANYO: SPA

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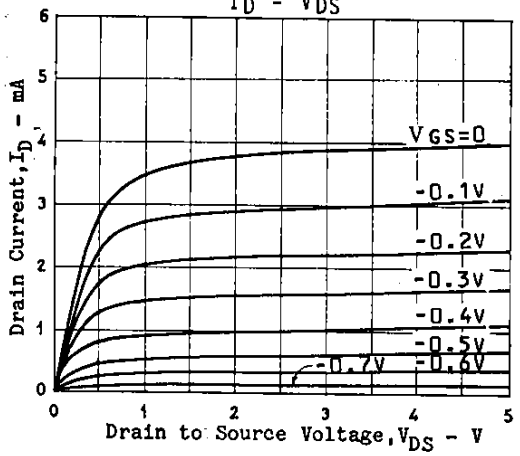
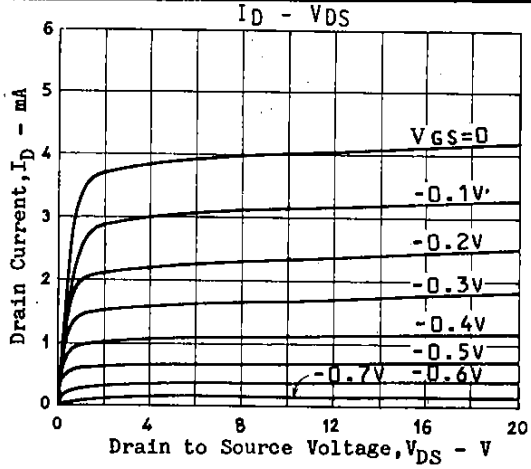
TOKYO OFFICE Tokyo Bldg.,1-10,1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

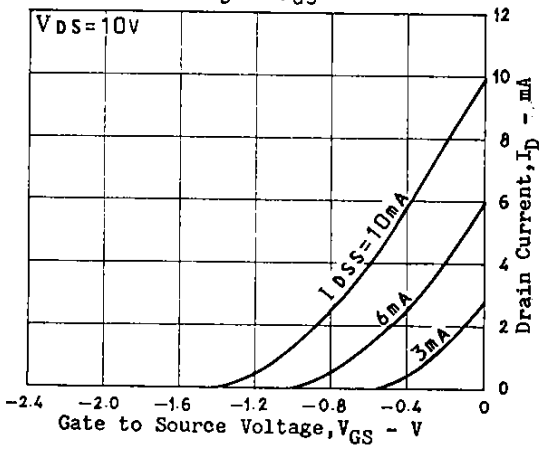
I_D - V_{DS}



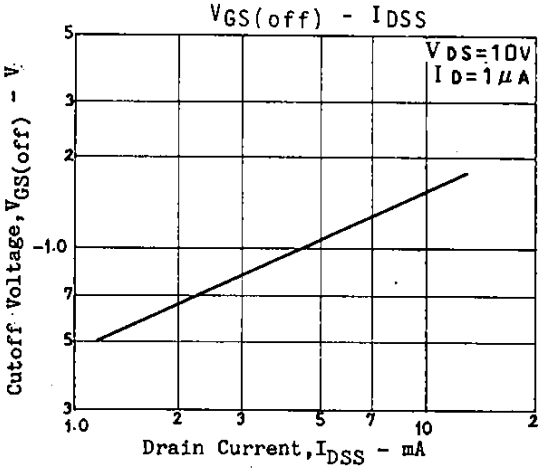
I_D - V_{DS}



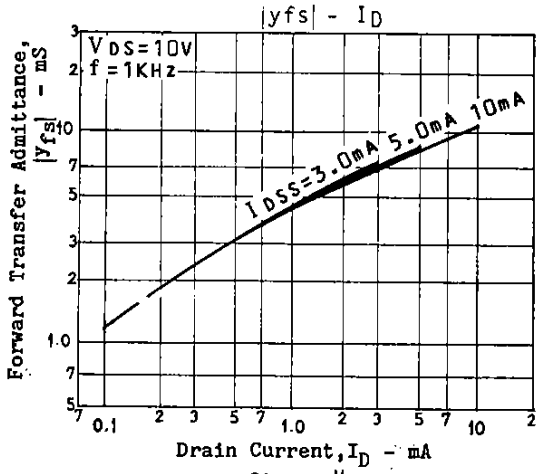
I_D - V_{GS}



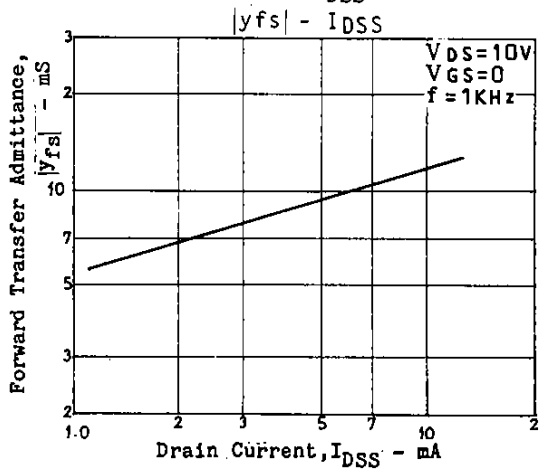
$V_{GS(off)}$ - I_{DSS}



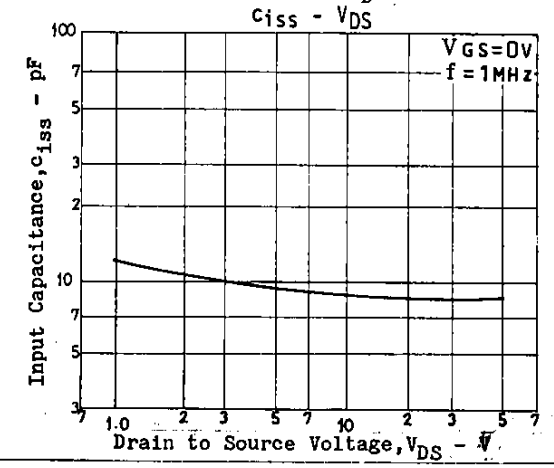
|yfs| - I_D



|yfs| - I_{DSS}



C_{iss} - V_{DS}



C_{rss} - V_{DS}